								RE	EVISI	ons										
LTR					DI	ESCR	IPTIC	N					D.	ATE :	(YR-MO	-DA)		APPRO	OVED	
LTR					DI	ESCR	IPTIC	М					D	ATE	(YR-MO	-DA)		APPRO	OVED	
DRV							<u> </u>	I						<u> </u>						
REV																				
SHEET																				
REV SHEET	15	16	17	18	19	20	21	22	23	24	25									
REV STATE				RE																
OF SHEETS					EET		1	2	3	4	5	6	7	8	9	10	11	12	13	14
PMIC N/A	, =				ARED B	Y f Bow	ling	•	<u> </u>	ום	EFENS				s su			TER		
STANDARDIZED CHECKED BY Jeff Bowling									AYTC	in, o	HIO	4544								
DRAWING APPROVED BY THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS				PAI	RALL		SYNC	HRO	NOUS			2K	X 9							
AND AGEN DEPARTMEN	CIES O	F THE		DRAWING APPROVAL DATE 94-07-06					SIZ			E CO				962-	9470)7		
AMSC N/A				REVI	SION L	EVEL.				A			5726					J4/\		
										SHI	ET	1	Of	:	,	25				
DESC FORM 193			-	<u> </u>						<u> </u>										

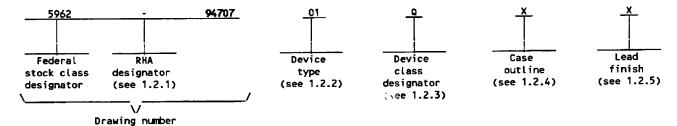
DISTRIBUTION STATEMENT A. Approved for public release; distribution is unlimited.

5962-E327-94

9004708 0003263 229

1. SCOPE

- 1.1 <u>Scope</u>. This drawing forms a part of a one part one part number documentation system (see 6.6 herein). Two product assurance classes consisting of military high reliability (device classes Q and M) and space application (device class V), and a choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). Device class M microcircuits represent non-JAN class B microcircuits in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices". When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN.
 - 1.2 PIN. The PIN shall be as shown in the following example:



- 1.2.1 <u>RHA designator</u>. Device class M RHA marked devices shall meet the MIL-I-38535 appendix A specified RHA levels and shall be marked with the appropriate RHA designator. Device classes Q and V RHA marked devices shall meet the MIL-I-38535 specified RHA levels and shall be marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.
 - 1.2.2 <u>Device type(s)</u>. The device type(s) shall identify the circuit function as follows:

Device type	Generic number 1/	<u>Circuit function</u>	Access time
01		2K x 9 CMOS Parallel Synchronous FIFO	50 ns
02 03		2K x 9 CMOS Parallel Synchronous FIFO 2K x 9 CMOS Parallel Synchronous FIFO	35 ns 25 ns

1.2.3 <u>Device class designator</u>. The device class designator shall be a single letter identifying the product assurance level as follows:

Device class

Device requirements documentation

М

Vendor self-certification to the requirements for non-JAN class B microcircuits in accordance with 1.2.1 of MIL-STD-883

Q or V

Certification and qualification to MIL-I-38535

1.2.4 Case outline(s). The case outline(s) shall be as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	<u>Terminals</u>	Package style
x	CQCC1-N32	32	Rectangular leadless chip carrier

1.2.5 <u>Lead finish</u>. The lead finish shall be as specified in MIL-STD-883 (see 3.1 herein) for class M or MIL-I-38535 for classes Q and V. Finish letter "X" shall not be marked on the microcircuit or its packaging. The "X" designation is for use in specifications when lead finishes A, B, and C are considered acceptable and interchangeable without preference.

1/ Generic numbers are listed on the Standardized Military Drawing Source Approval Bulletin at the end of this document and will also be listed in MIL-BUL-103 (see 6.7.2 herein).

STANDARDIZED MILITARY DRAWING	SIZE A		5962-94707
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 2

DESC FORM 193A JUL 91

002 71

9004708 0003264 165

1.3 Absolute maximum ratings. 2/ Maximum power dissipation (PD) 1.25 W Lead temperature (soldering, 10 seconds)-------+260°C Thermal resistance, junction-to-case (θ_{JC}): ---- See MIL-STD-1835 Junction temperature (T_J) - - - - - - - - +175°C 1.4 Recommended operating conditions. Supply voltage (GND)------ 0 V Input low voltage (VIL) - - - - - - - - - - 0.8 V dc maximum 1.5 Digital logic testing for device classes Q and V. Fault coverage measurement of manufacturing logic tests (MIL-STD-883, test method 5012) 3/ percent 2. APPLICABLE DOCUMENTS 2.1 Government specification, standards, bulletin, and handbook. Unless otherwise specified, the following specification, standards, bulletin, and handbook of the issue listed in that issue of the Department of Defense Index of Specifications and Standards specified in the solicitation, form a part of this drawing to the extent specified herein. SPECIFICATION MILITARY MIL-I-38535 - Integrated Circuits, Manufacturing, General Specification for. **STANDARDS** MILITARY MIL-STD-883 - Test Methods and Procedures for Microelectronics. MIL-STD-973 - Configuration Management.
MIL-STD-1835 - Microcircuit Case Outlines. BULLETIN MILITARY MIL-BUL-103 - List of Standardized Military Drawings (SMD's). HANDROOK MILITARY MIL-HDBK-780 - Standardized Military Drawings. (Copies of the specification, standards, bulletin, and handbook required by manufacturers in connection with specific acquisition functions should be obtained from the contracting activity or as directed by the contracting activity.) 2/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability. 3/ Values will be added when they become available. 5962-94707 **STANDARDIZED** SIZE MILITARY DRAWING A DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444 REVISION LEVEL SHEET 3

DESC FORM 193A JUL 91

■ 9004708 0003265 OT1 ■

2.2 <u>Non-Government publications</u>. The following document(s) form a part of this document to the extent specified herein. Unless otherwise specified, the issues of the documents which are DoD adopted are those listed in the issue of the DODISS cited in the solicitation. Unless otherwise specified, the issues of documents not listed in the DODISS are the issues of the documents cited in the solicitation.

AMERICAN SOCIETY FOR TESTING AND MATERIALS (ASTM)

ASTM Standard F1192-88 - Standard Guide for the Measurement of Single Event Phenomena from Heavy Ion Irradiation of Semiconductor Devices.

(Applications for copies of ASTM publications should be addressed to the American Society for Testing and Materials, 1916 Race Street, Philadelphia, PA 19103.)

ELECTRONICS INDUSTRIES ASSOCIATION (EIA)

JEDEC Standard No. 17 - A Standardized Test Procedure for the Characterization of Latch-up in CMOS Integrated Circuits.

(Applications for copies should be addressed to the Electronics Industries Association, 2001 Pennsylvania Street, N.W., Washington, DC 20006.)

(Non-Government standards and other publications are normally available from the organizations that prepare or distribute the documents. These documents also may be available in or through libraries or other informational services.)

2.3 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing shall take precedence.

3. REQUIREMENTS

- 3.1 <u>Item requirements</u>. The individual item requirements for device class M shall be in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices" and as specified herein. The individual item requirements for device classes Q and V shall be in accordance with MIL-1-38535, the device manufacturer's Quality Management (QM) plan, and as specified herein.
- 3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-STD-883 (see 3.1 herein) for device class M and MIL-I-38535 for device classes Q and V and herein.
 - 3.2.1 Case outline(s). The case outline(s) shall be in accordance with 1.2.4 herein.
 - 3.2.2 <u>Terminal connections</u>. The terminal connections shall be as specified on figure 1.
 - 3.2.3 Truth table(s). The truth table(s) shall be as specified on figure 2.
- 3.2.4 <u>Radiation exposure circuit</u>. The radiation exposure circuit will be provided when RHA product becomes available.
- 3.3 <u>Electrical performance characteristics and postirradiation parameter limits</u>. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full case operating temperature range.
- 3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table IIA. The electrical tests for each subgroup are defined in table 1.
- 3.5 Marking. The part shall be marked with the PIN listed in 1.2 herein. Marking for device class M shall be in accordance with MIL-STD-883 (see 3.1 herein). In addition, the manufacturer's PIN may also be marked as listed in MIL-BUL-103. Marking for device classes Q and V shall be in accordance with MIL-I-38535.
- 3.5.1 <u>Certification/compliance mark</u>. The compliance mark for device class M shall be a "C" as required in MIL-STD-883 (see 3.1 herein). The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-I-38535.

STANDARDIZED MILITARY DRAWING	SIZE A		5962-94707
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 4

DESC FORM 193A JUL 91

■ 9004708 0003266 T38 **■**

- 3.6 Certificate of compliance. For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-BUL-103 (see 6.7.2 herein). For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.7.1 herein). The certificate of compliance submitted to DESC-EC prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device class M, the requirements of MIL-STD-883 (see 3.1 herein), or for device classes Q and V, the requirements of MIL-1-38535 and the requirements herein.
- 3.7 <u>Certificate of conformance</u>. A certificate of conformance as required for device class M in MIL-STD-883 (see 3.1 herein) or for device classes Q and V in MIL-I-38535 shall be provided with each lot of microcircuits delivered to this drawing.
- 3.8 Notification of change for device class M. For device class M, notification to DESC-EC of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change as defined in MIL-STD-973.
- 3.9 <u>Verification and review for device class M</u>. For device class M, DESC, DESC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.
- 3.10 <u>Microcircuit group assignment for device class M</u>. Device class M devices covered by this drawing shall be in microcircuit group number 105 (see MIL-1-38535, appendix A).

4. QUALITY ASSURANCE PROVISIONS

- 4.1 <u>Sampling and inspection</u>. For device class M, sampling and inspection procedures shall be in accordance with MIL-STD-883 (see 3.1 herein). For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-I-38535 and the device manufacturer's QM plan.
- 4.2 <u>Screening</u>. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. For device classes Q and V, screening shall be in accordance with MIL-I-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection.
 - 4.2.1 Additional criteria for device class M.
 - a. Delete the sequence specified as initial (preburn-in) electrical parameters through interim (postburn-in) electrical parameters of method 5004 and substitute lines 1 through 6 of table IIA herein.
 - b. For device class M, the test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. For device class M, the test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
 - (1) Dynamic burn-in for device class M (method 1015 of MIL-STD-883, test condition D; for circuit, see 4.2.1b herein).
 - c. Interim and final electrical parameters shall be as specified in table IIA herein.
 - 4.2.2 Additional criteria for device classes Q and V.
 - a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-I-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-I-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
 - b. Interim and final electrical test parameters shall be as specified in table IIA herein.
 - c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in appendix B of MIL-I-38535.

STANDARDIZED MILITARY DRAWING	SIZE A		5962-94707
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 5

DESC FORM 193A JUL 91

= 9004708 0003267 974 **=**

TABLE I. <u>Electrical performance characteristics</u>.

Test	Symbol	Conditions -55°C ≤ T _C ≤ +125°C	Group A	Device	Li	mit	Unit
		4.5 V ≤ V _{CC} ≤ 5.5 V unless otherwise specified	subgroups	type	Min	Max	
Input leakage current	ILI	0.4 V ≤ V _{IN} ≤ V _{CC}	1,2,3	ALL	-10	+10	μА
Output leakage current	ILO	$\overline{OE} \ge V_{IH}, 0.4 \le V_{OUT} \le V_{CC}$	1,2,3	All	-10	+10	μΑ
Output high voltage	VOH	I _{OH} = -2 mA	1,2,3	ALL	2.4		٧
Output low voltage	VOL	I _{OL} = 8 mA	1,2,3	ALL		0.4	V
Active power supply current	Icc	f = 20 MHz, outputs open	1,2,3	ALL		180	mA
Input capacitance	CIN	V _{IN} = 0 V, f = 1.0 MHz, T _A = +25°C, see 4.4.1e	4	All		10	pF
Output capacitance	C _{OUT}	V _{OUT} = 0 V, f = 1.0 MHz, with output deselected (OE = high), T _A = +25°C, see 4.4.1e	4	All		10	рF
Functional tests		See 4.4.1c	7,8A,8B	All		<u> </u>	
Clock cycle frequency	fs	C _L = 30 pF, input pulse	9,10,11	01		20	MHZ
		levels = GND to 3.0 V, input rise/fall times = 3 ns,		02		28.6	
		input/output timing reference levels = 1.5 V,		03		40	Ī
Data access time	t _A	see figures 3 and 4	9,10,11	01	3	25	ns
		·		02	3	20	_
				03	3	15	
Clock cycle time	tCLK		9,10,11	01	50		ns
				02	35		1
				03	25	<u> </u>	
Clock high time	†CLKH	1	9,10,11	01	20		ns
				02	14		
				03	10		
Clock low time	tCLKL	1	9,10,11	01	20		ns
				02	14		
				03	10		
Data setup time	t _{DS}]	9,10,11	01	10		ns
				02	8		
				03	6		
First read latency time	tFRL		9,10,11	All		1/	

See footnotes at end of table.

STANDARDIZED MILITARY DRAWING	SIZE A		5962-94707
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 6

DESC FORM 193A JUL 91

9004708 0003268 800 **m**

TABLE I. <u>Electrical performance characteristics</u> - Continued.

Test	Symbol	Conditions $-55^{\circ}C \leq T_{C} \leq +125^{\circ}C$	Group A	Device	e Limit		Unit
		4.5 V ≤ V _{CC} ≤ 5.5 V unless otherwise specified	subgroups	type	Mîn	Max	
Data hold time	t _{DH}	C _L = 30 pF, input pulse	9,10,11	01,02	2		ns
		levels = GND to 3.0 V, input rise/fall times = 3 ns,		03	1		
Enable setup time	^t ens	input/output timing reference levels = 1.5 V,	9,10,11	01	10		ns
		see figures 3 and 4		02	8		
				03	6		
Enable hold time	tENH		9,10,11	01,02	2		ns
			. <u></u>	03	1		
Reset pulse width <u>2</u> /	t _{RS}		9,10,11	01	50		ns
				02	35		
				03	25		
Reset setup time	t _{RSS}		9,10,11	01	50		ns
				02	35		
				03	25		_
Reset recovery time	^t rsr		9,10,11	01	50		ns
				02	35		_
				03	25		<u> </u>
Reset to flag and output time	tRSF		9,10,11	01		50	ns
	Ì		ļ	02		35	_
				03		25	
Output enable to output in low Z <u>3</u> /	t _{OLZ}		9,10,11	All	0		ns
Output enable to output valid	toE		9,10,11	01	3	28	ns
				02	3	15	
				03	3	13	
Output enable to output in	^t OHZ		9,10,11	01	3	28	ns
high Z <u>3</u> /				02	3	15	
				03	3	13	

See footnotes at end of table.

STANDARDIZED MILITARY DRAWING	SIZE		5962-94707
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 7

DESC FORM 193A JUL 91

■ 9004708 0003269 747 **■**

TABLE I. <u>Electrical performance characteristics</u> - Continued.

Test	Symbol	Conditions -55°C ≤ T _C ≤ +125°C	Group A	Device	Limit		Unit
		4.5 V ≤ V _{CC} ≤ 5.5 V unless otherwise specified	subgroups	type	Min	Max	
Write clock to full flag	twff	C _L = 30 pF, input pulse	9,10,11	01		30	ns
		levels = GND to 3.0 V, input rise/fall times = 3 ns,		02		20	
		input/output timing reference levels = 1.5 V,		03		15	
Read clock to empty flag	t _{REF}	see figures 3 and 4	9,10,11	01		30	ns
				02		20]
				03		15	
Read Clock to programmable	t _{PAE}	9,10,11	01		30	ns	
almost-empty flag				02		20]
				03		15	
Write Clock to programmable	t _{PAF}		9,10,11	01		30	ns
almost-full flag				02		20	
				03		15	
Skew time between read clock	tsKEW1		9,10,11	01	15		ns
& full flag	e clock for empty flag lag			02	12		
				03	10		
Skew time between read clock	tskew2		9,10,11	01	45		ns
and write clock for Almost- Empty Flag & Almost-Full Flag				02	42		
				03	40		

^{1/} When t_{SKEW1} ≥ the minimum limit, t_{FRL} (maximum) = t_{CLK} + t_{SKEW1}. When t_{SKEW1} < the minimum limit, t_{FRL} (maxi<u>mu</u>m) = either 2t_{CLK} + t_{SKEW1} or t_{CLK} + t_{SKEW1}. The latency timing applies only at the empty boundary (EF = LOW).

- $\underline{2}/$ Pulse widths less than the minimum values specified are not allowed.
- $\underline{\mathbf{3}}/$ If not tested, shall be guaranteed to the limits specified in table I.

STANDARDIZED MILITARY DRAWING	SIZE A		5962-94707
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 8

9004708 0003270 469

Device type	All
Case outline	x
Terminal number	Terminal symbol
1	D ₅
2	04
3	03
4	D ₂
5	D ₁
6	D _O
7	PAF
8	PAE
9	GND
10	REN1
11	RCLK
12	REN2
13	ŌE
14	EF
15	FF
16	e 0
17	a ₁
18	Q ₂
19	Q ₃
20	94
21	۵ ₅
22	a ₆
23	a ₇
24	a ₈
25	v _{cc}
26	WEN2/LD
27	WCLK
28	WEN1
29	RS
30	D ₈
31	D ₇
32	D ₆
	. 6

FIGURE 1. <u>Terminal connections</u>.

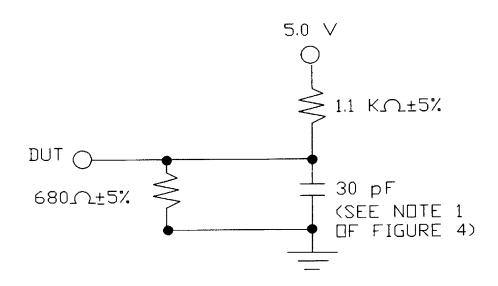
STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER	SIZE A		5962-94707
DAYTON, OHIO 45444		REVISION LEVEL	SHEET 9

🖿 9004708 0003271 3T5 🖿

No. of words in FIFO	FF	PAF	PAE	EF
0	Н	н	L	L
1 to n	н	н	L	Н
(n+1) to (2048-(m+1)) 1/	Н	Н	Н	н
(2048-m) to 2047 <u>2</u> /	Н	L	н	н
2048	L	L	н	Н

 $[\]frac{1}{2}$ / n = empty offset (n = 7 default value). $\frac{1}{2}$ / m = full offset (m = 7 default value).

FIGURE 2. Truth table.



AC test conditions:

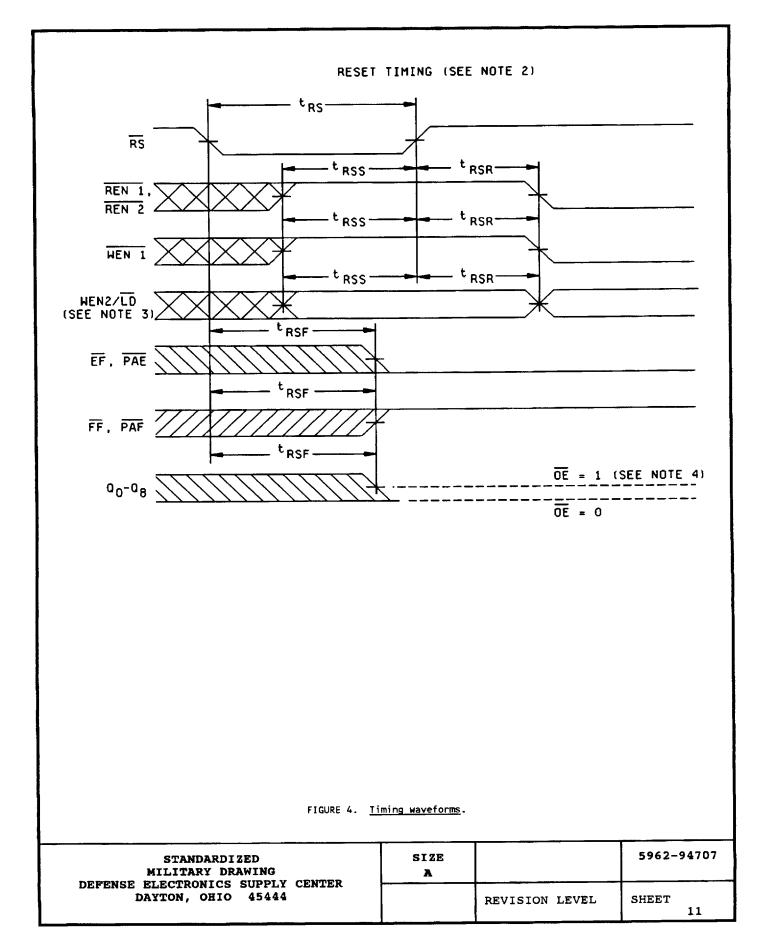
Input pulse levels: GND to 3.0 V
Input rise/fall times: ≤ 3 ns/V
Input timing reference levels: 1.5 V
Output reference levels: 1.5 V

FIGURE 3. Output load circuit.

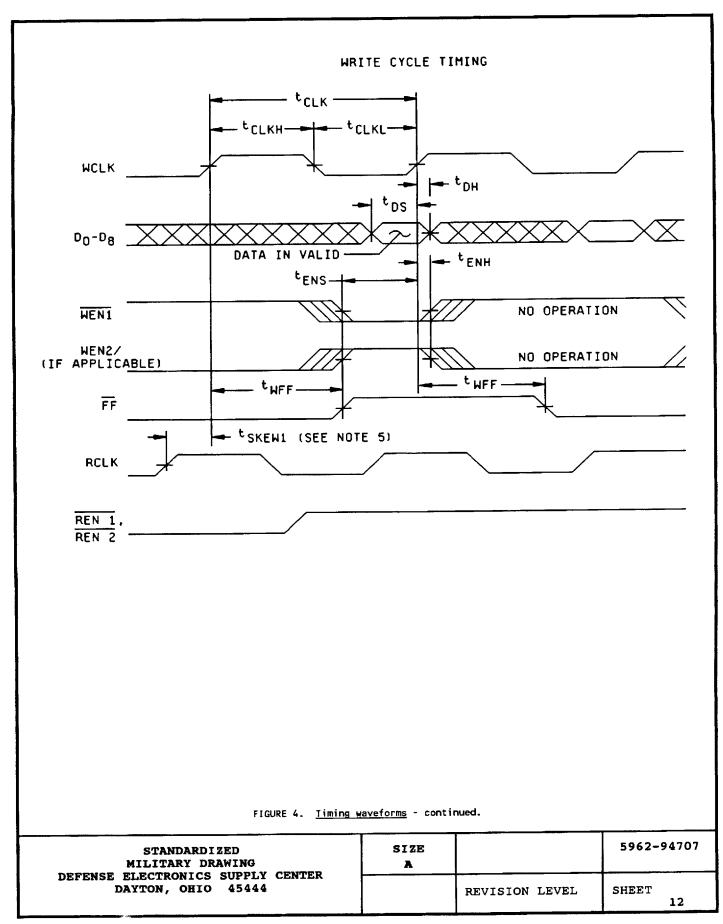
STANDARDIZED MILITARY DRAWING	SIZE A		5962-94707
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 10

DESC FORM 193A JUL 91

■ 9004708 0003272 231 ■

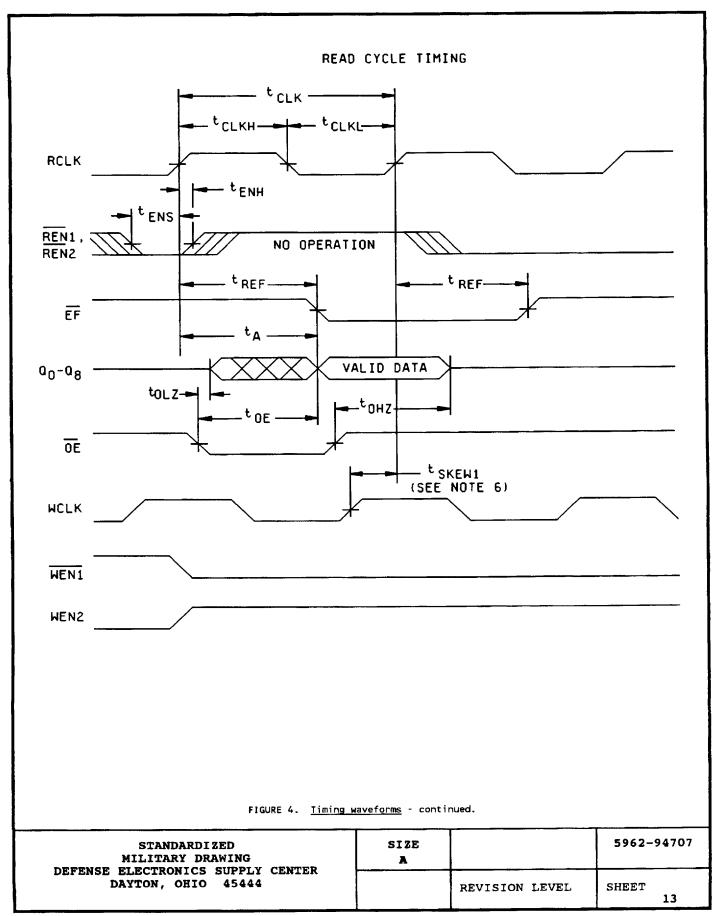


9004708 0003273 178

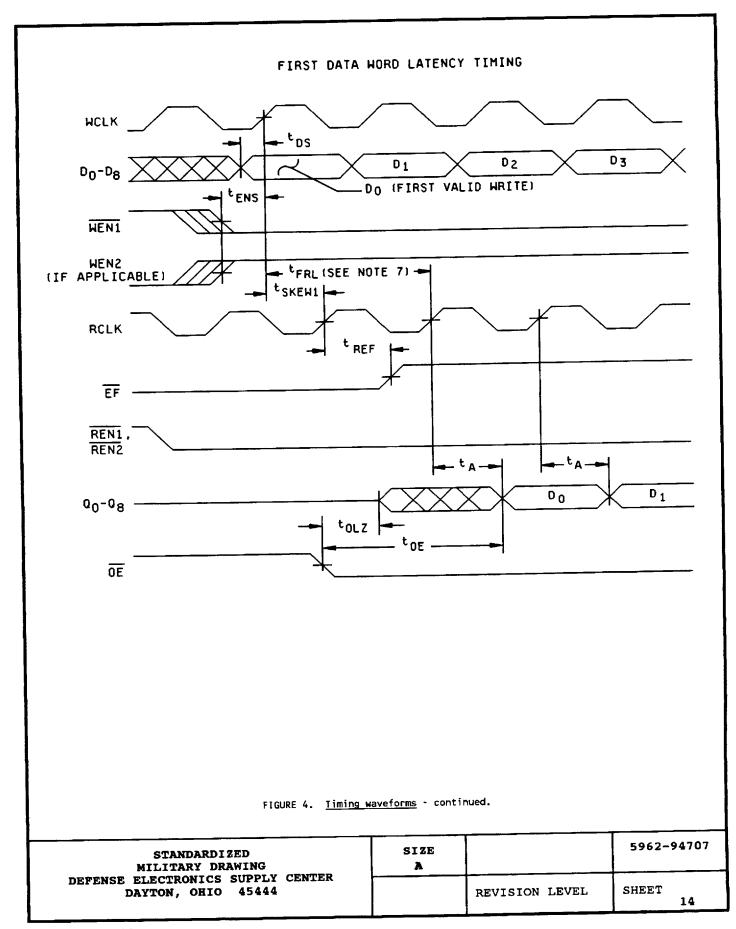


DESC FORM 19.3

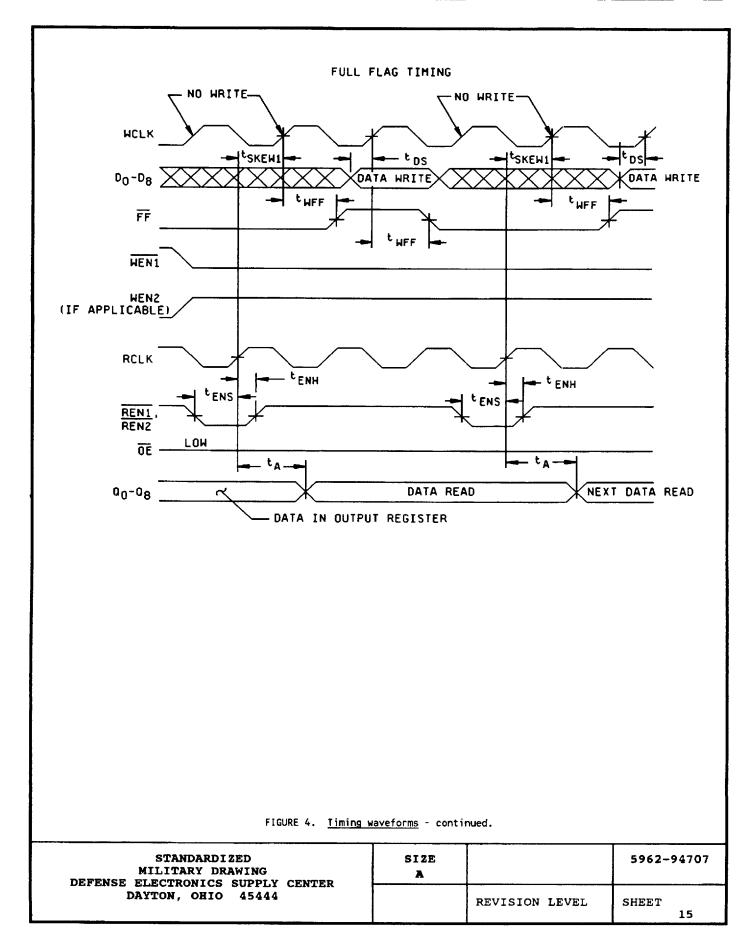
■ 4004708 0003274 004 **■**



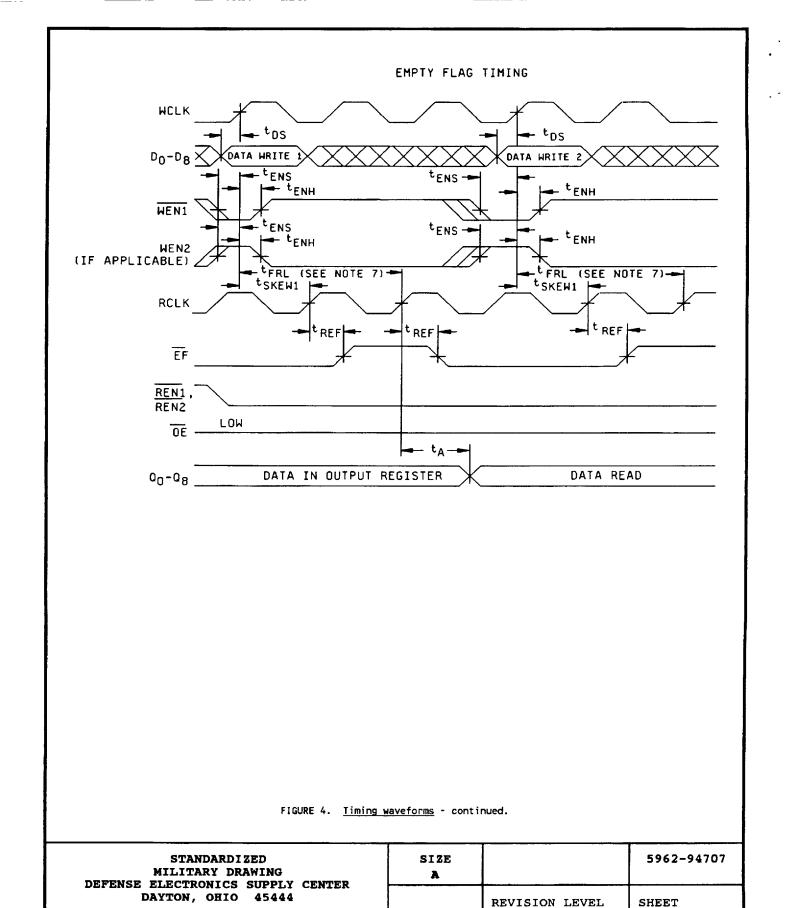
= 9004708 0003275 T40 =



■ 9004708 0003276 987 **■**



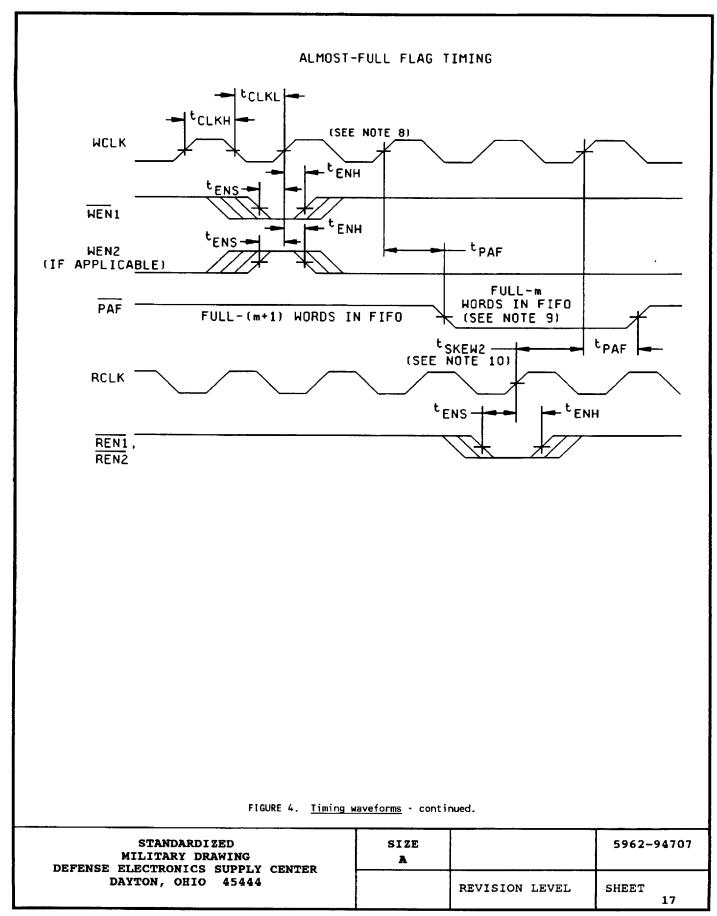
9004708 0003277 813 -



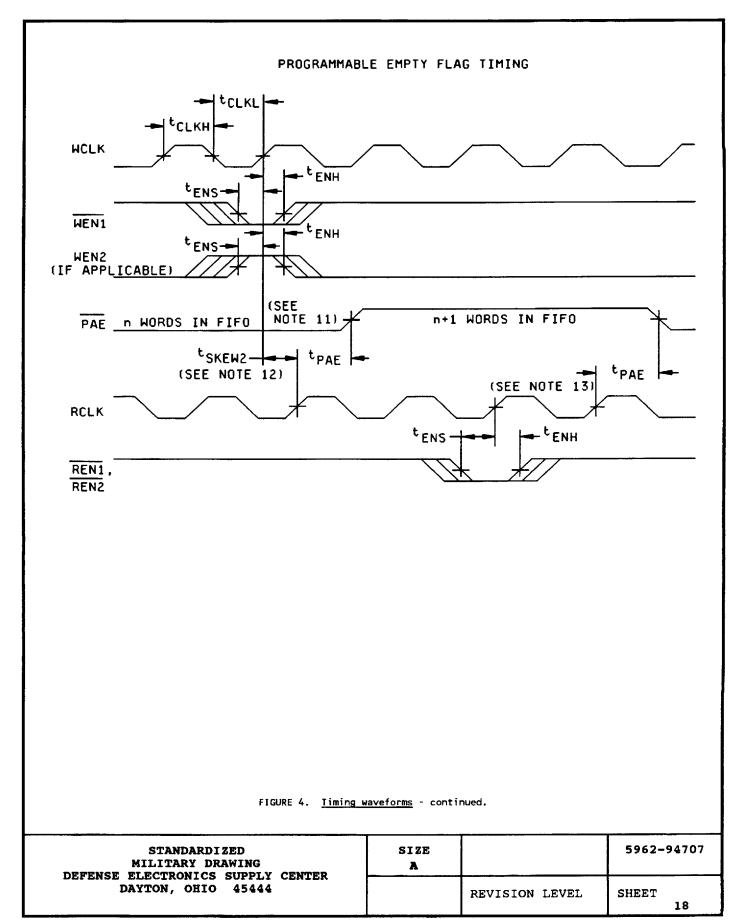
16

DESC FORM 193A JUL 91

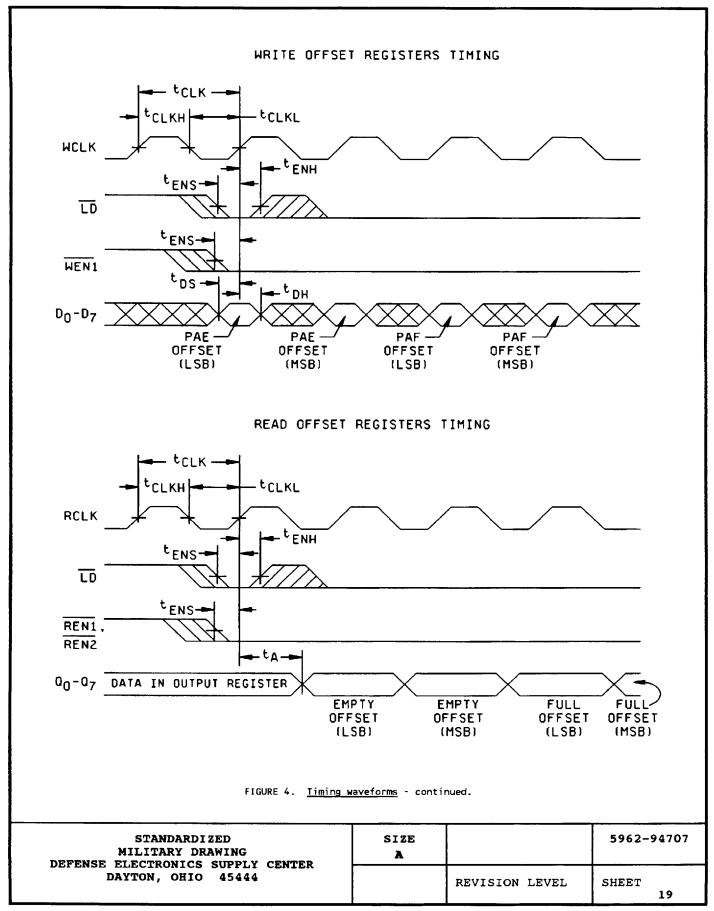
■ 9004708 0003278 75T ■



■ 9004708 0003279 696 ■



- 9004708 0003280 308 **-**



= 9004708 0003281 244 =

NOTES:

- 1. C_i = load capacitance and includes jig and probe capacitance.
- 2. The clocks (RCLK, WCLK) can be free-running during reset.
- 3. Holding WEN2/LD high during reset will make the pin act as a second write enable pin. Holding WEN2/LD low during reset will make the pin act as a load enable for the programmable flag offset registers.
- 4. After reset, the outputs will be low if \overline{OE} = low and tri-state if \overline{OE} = high.
- 5. t_{SKEW1} is the minimum time between a rising RCLK edge and a rising WCLK edge to guarantee that FF will go high during the current clock cycle. If the time between the rising edge of RCLK and the rising edge of WCLK is less than t_{SKEW1}, then FF may not change state until the next WCLK edge.
- 6. t_{SKEW1} is the minimum time between a rising WCLK edge and a rising RCLK edge to guarantee that EF will go high during the current clock cycle. If the time between the rising edge of WCLK and the rising edge of RCLK is less than t_{SKEW1}, then EF may not change state until the next RCLK edge.
- 7. When $t_{SKEW1} \ge$ the minimum limit specified in table I, t_{FRL} (maximum) = t_{CLK} + t_{SKEW1} . When t_{SKEW1} < the minimum limit, t_{FRL} (maximum) = either $2t_{CLK}$ + t_{SKEW1} or t_{CLK} + t_{SKEW1} . The latency timing applies only at the empty boundary (EF = LOW).
- If a write is performed on this rising edge of the write clock, there will be Full-6 words in the FIFO when AF
 goes low.
- 9. 2048 m words.
- 10. t_{SKEW2} is the minimum time between a rising RCLK edge and a rising WCLK edge for AF to change during the current clock cycle. If the time between the rising edge of RCLK and the rising edge of WCLK is less than t_{SKEW2}, then AF may not change state until the next WCLK edge.
- 11. PAE offset = n.
- 12. t_{SKEW2} is the minimum time between a rising WCLK edge and a rising RCLK edge for PAE to change during the current clock cycle. If the time between the rising edge of WCLK and the rising edge of RCLK is less than t_{SKEW2}, then PAE may not change state until the next RCLK rising edge.
- 13. If a read is performed on this rising edge of the read clock, there will be Empty+n-1 words in the FIFO when PAE goes low.

FIGURE 4. Timing waveforms - continued.

STANDARDIZED MILITARY DRAWING	SIZE A		5962-94707
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 20

DESC FORM 193A JUL 91

🖿 9004708 0003282 lao 🖿

TABLE IIA. <u>Electrical test requirements</u>. <u>1</u>/ <u>2</u>/ <u>3</u>/ <u>4</u>/ <u>5</u>/ <u>6</u>/ <u>7</u>/

Line no.	Test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)	Subgr (in accord MIL-I-38535,	lance with
110.	requirements	Device class M	Device class Q	Device class V
1	Interim electrical parameters (see 4.2)		1,7,9	1,7,9
2	Static burn-in I and II (method 1015)	Not required	Not required	Required
3	Same as line 1			1*,7* A
4	Dynamic burn-in (method 1015)	Required	Required	Required
5	Same as line 1			1*,7* A
6	Final electrical parameters	1*,2,3,7*, 8A,8B,9,10, 11	1*,2,3,7*, 8A,8B,9,10,	1*,2,3,7*, 8A,8B,9, 10,11
7	Group A test requirements	1,2,3,4**,7, 8A,8B,9,10, 11	1,2,3,4**,7, 8A,8B,9,10, 11	1,2,3,4**,7, 8A,8B,9,10,
8	Group C end-point electrical parameters	2,3,7, 8A,8B	1,2,3,7, 8A,8B Δ	1,2,3,7, 8A,8B,9, 10,11 Δ
9	Group D end-point electrical parameters	2,3, 8A,8B	2,3, 8A,8B	2,3, 8A,8B
10	Group E end-point electrical parameters	1,7,9	1,7,9	1,7,9

^{1/} Blank spaces indicate tests are not applicable.

7/ See 4.4.1d.

STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER	SIZE A		5962-94707
DAYTON, OHIO 45444		REVISION LEVEL	SHEET 21

DESC FORM 193A JUL 91

9004708 0003283 017

 $[\]overline{2}$ / Any or all subgroups may be combined when using high-speed testers.

^{3/} Subgroups 7 and 8 functional tests shall verify the truth table.

 $[\]frac{4}{4}$ * indicates PDA applies to subgroup 1 and 7.

<u>5</u>/ ** see 4.4.1e.

^{\(\}textit{\Delta} \) / \(\textit{\Delta} \) indicates delta limit (see table IIB) shall be required where specified, and the delta values shall be computed with reference to the previous interim electrical parameters (see line 1).

TABLE IIB. Delta limits at +25°C.

Test <u>1</u> /	Device types
tLI	±10% of specified value in table I
ILO	±10% of specified value in table I

- 1/ The above parameters shall be recorded before and after the required burn-in and life tests to determine the delta.
- 4.3 <u>Qualification inspection for device classes Q and V</u>. Qualification inspection for device classes Q and V shall be in accordance with MIL-I-38535. Inspections to be performed shall be those specified in MIL-I-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).
- 4.4 <u>Conformance inspection</u>. Quality conformance inspection for device class M shall be in accordance with MIL-STD-883 (see 3.1 herein) and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4). Technology conformance inspection for classes Q and V shall be in accordance with MIL-I-38535 including groups A, B, C, D, and E inspections and as specified herein except where option 2 of MIL-I-38535 permits alternate in-line control testing.

4.4.1 Group A inspection.

- a. Tests shall be as specified in table IIA herein.
- b. Subgroups 5 and 6 of table I of method 5005 of MIL-STD-883 shall be omitted.
- c. For device class M, subgroups 7 and 8 tests shall be sufficient to verify the truth table. For device classes Q and V, subgroups 7 and 8 shall include verifying the functionality of the device; these tests shall have been fault graded in accordance with MIL-STD-883, test method 5012 (see 1.5 herein).
- d. O/V (latch-up) tests shall be measured only for initial qualification and after any design or process changes which may affect the performance of the device. For device class M, procedures and circuits shall be maintained under document revision level control by the manufacturer and shall be made available to the preparing activity or acquiring activity upon request. For device classes Q and V, the procedures and circuits shall be under the control of the device manufacturer's TRB in accordance with MIL-I-38535 and shall be made available to the preparing activity or acquiring activity upon request. Testing shall be on all pins, on five devices with zero failures. Latch-up test shall be considered destructive. Information contained in JEDEC Standard number 17 may be used for reference.
- e. Subgroup 4 (C_{IN} and C_{OUT} measurements) shall be measured only for initial qualification and after any process or design changes which may affect input or output capacitance. Capacitance shall be measured between the designated terminal and GND at a frequency of 1 MHz. Sample size is 15 devices with no failures, and all input and output terminals tested.
- 4.4.2 <u>Group C inspection</u>. The group C inspection end-point electrical parameters shall be as specified in table IIA herein. Delta limits shall apply only to subgroup 1 of group C inspection and shall consist of tests specified in table IIB herein.

STANDARDIZED MILITARY DRAWING	SIZE A		5962-94707
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 22

DESC FORM 193A JUL 91

■ 9004708 0003284 T53 **■**

- 4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:
 - a. Test condition D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005.
 - b. $T_A = +125$ °C, minimum.
 - c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.
- 4.4.2.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-I-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB, in accordance with MIL-I-38535, and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005.
- 4.4.3 <u>Group D inspection</u>. The group D inspection end-point electrical parameters shall be as specified in table IIA herein.
- 4.4.4 <u>Group E inspection</u>. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein). RHA levels for device classes Q and V shall be M, D, R, and H and for device class M shall be M and D.
 - a. End-point electrical parameters shall be as specified in table IIA herein.
 - b. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-1-38535, appendix A, for the RHA level being tested. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-I-38535 for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table 1 at T_A = +25°C ±5°C, after exposure, to the subgroups specified in table IIA herein.
 - c. When specified in the purchase order or contract, a copy of the RHA delta limits shall be supplied.
- 4.5 <u>Delta measurements for device classes Q and V</u>. Delta measurements, as specified in table IIA, shall be made and recorded before and after the required burn-in screens and steady-state life tests to determine delta compliance. The electrical parameters to be measured, with associated delta limits are listed in table IIB. The device manufacturer may, at his option, either perform delta measurements or within 24 hours after burn-in perform final electrical parameter tests, subgroups 1, 7, and 9.
 - 5. PACKAGING
- 5.1 <u>Packaging requirements</u>. The requirements for packaging shall be in accordance with MIL-STD-883 (see 3.1 herein) for device class M and MIL-I-38535 for device classes Q and V.
 - 6. NOTES

(This section contains information of a general or explanatory nature that may be helpful, but is not mandatory.)

- 6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.
- 6.1.1 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
 - 6.1.2 <u>Substitutability</u>. Device class Q devices will replace device class M devices.
- 6.2 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-973 using DD Form 1692, Engineering Change Proposal.

STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER	SIZE A		5962-94707
DAYTON, OHIO 45444		REVISION LEVEL	SHEET 23

DESC FORM 193A JUL 91

■ 9004708 0003285 99T ■

- 6.3 <u>Record of users</u>. Military and industrial users shall inform Defense Electronics Supply Center when a system application requires configuration control and which SMD's are applicable to that system. DESC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DESC-EC, telephone (513) 296-6047.
- 6.4 <u>Comments</u>. Comments on this drawing should be directed to DESC-EC, Dayton, Ohio 45444-5270, or telephone (513) 296-5377.
 - 6.5 Symbols, definitions, and functional descriptions.

Symbol	Name	1/0	Description
D0-D8	Data Inputs	1	Data inputs for a 9-bit bus.
RS	Reset	1	When RS is set low, internal read and write pointers are <u>set</u> to the first <u>location of</u> the RAM array, FF and PAF go high, and PAE and EF go low. A reset is required before an initial WRITE after power-up.
WCLK	Write Clock	I	When WEN is low, data is written into the FIFO on a low-to-high transition of WCLK, if the FIFO is not full.
WEN	Write Enable	I	When WEN is low, data is written into the F <u>IFO</u> on every low-to-high transition of WCLK. When WEN is high, the FIFO holds the previous data. Data will not be written into the FIFO if the FF is low.
RCLK	Read Clock	I	When $\overline{\text{REN}}$ is low, data $\overline{\text{is r}}$ ead from the FIFO on a low-to-high transition of $\overline{\text{RCLK}}$, if the FIFO is not empty.
REN	Read Enable	I	When REN is low, data is read from the FIFO on every low-to-high transition of RCLK. When REN is high, the output register holds the previous data. Data will not be read from the FIFO if the EF is LOW.
ŌĒ	Output Enable	I	When OE is low, the data output bus is active. If OE is high, the output data bus will be in a high impedance state.
EF	Empty Flag	0	When EF is low, the FIFO is empty and further data reads from the output are inhibited. When EF is high, the FIFO is not empty. EF is synchronized to RCLK.
FF	Full Flag	0	When FF is low, the FIFO is full and further data writes into the input are inhibited. When FF is high, the FIFO is not full. FF is syncchronized to WCLK.
QQ-Q8	Data Outputs	0	Data ouputs for a 9-bit bus.
v _{cc}	Power	-	+5 volt power supply pin.
GND	Ground	 	Ground pin.

6.5.1 <u>Timing limits</u>. The table of timing values shows either a minimum or a maximum limit for each parameter. Input requirements are specified from the external system point of view. Thus, address setup time is shown as a minimum since the system must supply at least that much time (even though most devices do not require it). On the other hand, responses from the memory are specified from the device point of view. Thus, the access time is shown as a maximum since the device never provides data later than that time.

STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER	SIZE A		5962-94707
DAYTON, OHIO 45444		REVISION LEVEL	SHEET 24

DESC FORM 193A JUL 91

■ 9004708 0003286 826 **■**

6.5.2 Waveforms.

Waveform symbol	Input	Output	
	MUST BE VALID	WILL BE VALID	
711111	CHANGE FROM H TO L	WILL CHANGE FROM H TO L	
_/////	CHANGE FROM L TO H	WILL CHANGE FROM L TO H	
XXXXXXX	DON'T CARE ANY CHANGE PERMITTED	CHANGING STATE UNKNOWN	
		HIGH IMPEDANCE	

6.6 One part - one part number system. The one part - one part number system described below has been developed to allow for transitions between identical generic devices covered by the three major microcircuit requirements documents (MIL-H-38534, MIL-I-38535, and 1.2.1 of MIL-STD-883) without the necessity for the generation of unique PIN's. The three military requirements documents represent different class levels, and previously when a device manufacturer upgraded military product from one class level to another, the benefits of the upgraded product were unavailable to the Original Equipment Manufacturer (OEM), that was contractually locked into the original unique PIN. By establishing a one part number system covering all three documents, the DEM can acquire to the highest class level available for a given generic device to meet system needs without modifying the original contract parts selection criteria.

Military documentation format	Example PIN under new system	Manufacturing source listing	Document <u>listing</u>
New MIL-H-38534 Standardized Military Drawings	5962-XXXXXZZ(H or K)YY	QML - 38534	MIL-BUL-103
New MIL-1-38535 Standardized Military Drawings	5962-XXXXXZZ(Q or V)YY	QML-38535	MIL-BUL-103
New 1.2.1 of MIL-STD-883 Standardized Military Drawings	5962-XXXXXZZ(M)YY	MIL-BUL-103	MIL-BUL-103

6.7 Sources of supply.

- 6.7.1 <u>Sources of supply for device classes Q and V</u>. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DESC-EC and have agreed to this drawing.
- 6.7.2 <u>Approved sources of supply for device class M</u>. Approved sources of supply for class M are listed in MIL-BUL-103. The vendors listed in MIL-BUL-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DESC-EC.

STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444	SIZE A		5962-94707
		REVISION LEVEL	SHEET 25

DESC FORM 193A JUL 91

■ 9004708 0003287 762 **■**